CLAIMS

1) An integrated apparatus for optical monitoring of semiconductor workpiece for process control in the semiconductor production process, comprising;

a supporting assembly for supporting said workpiece

an optical monitoring unit accommodated opposite the surface of said workpiece and separated therefrom by an optical window, said optical monitoring unit is mounted for reciprocating movement within a plane parallel to said window for monitoring at least one desired parameter of said semiconductor workpiece and having a pattern recognition and an auto-focusing utilities;

wherein said optical window comprises one or a plurality of relatively small window fragments located in pre-determined locations to enable observation of desired pre-determined portions of said workpiece,

and wherein the size and shape of said window fragments are selected according to the requirements of transparency in a pre-determined spectral range, mechanical strength and ability of pattern recognition and auto-focusing.

- 2) Integrated apparatus according to claim 1 wherein said desired portions of the workpiece include the center and part of the edge of said workpiece.
- 3) Integrated apparatus according to claim 2 wherein at least one of said optical window fragments is of a circle's sector shape.

- 4) Integrated apparatus according to claim 2 wherein at least one of said optical window fragments is of a rectangular shape.
- 5) Integrated apparatus according to claims 4 wherein said window fragments comprise at least one additional window fragment having a bent strip-like shape around the workpiece' edge
- 6) Integrated apparatus according to claim 1 wherein said optical monitoring unit comprising a spectrophotometer.
- 7) Integrated apparatus according to claim 1 wherein said optical monitoring unit comprising an ellipsometer.
- 8) Integrated apparatus according to claim 1 wherein said semiconductor workpiece is a wafer.
- 9) An integrated apparatus according to claim 1 for optical monitoring semiconductor workpiece having an axis of symmetry, wherein said supporting assembly is mounted for substantially slow rotation.
- 10) A method for optical monitoring semiconductor workpiece having an axis of symmetry for process control in the semiconductor production process comprising the steps of;

optical scanning the workpiece using movable optical unit through optical window designed as a plurality of relatively small fragments located in pre-determined locations to enable observation of desired portions of the workpiece, wherein the size and shape of said fragments being selected according to the requirements of transparency in the pre-determined spectral range, mechanical strength and ability of pattern recognition and auto-focusing;

and defining at least one desired parameter of said semiconductor workpiece at said desired portions of the.

- 11) Method for optical monitoring semiconductor workpiece according to claim 10 wherein said desired portions of the workpiece include the center and part of the edge of said workpiece.
- 12) Method for optical monitoring semiconductor workpiece according to claim 10 further comprising rotation of said workpiece by a pre-determined angle.
- 13) Method for optical monitoring semiconductor workpiece according to claim 10 wherein the track of said optical scanning is designed in such manner that enables pattern recognition and autofocusing.
- 14) Method for optical monitoring semiconductor workpiece according to claim 10 wherein said workpiece has a multi-layer structure and at least one desired parameter is a thickness of at least one of the workpiece' layers.
- 15) Method for optical monitoring semiconductor workpiece according to claim 14 wherein said optical scanning includes measuring of spectral characteristics of light response of the scanned portions of the workpiece.